



## IR207DM16CCB

**STANDARD RECOVERY DIODES**

- Junction Size: Rectangular 207 x 157 mils
- Wafer Size: 4"
- $V_{RRM}$  Class: 1600 V
- Passivation Process: Glassivated MOAT
- Reference IR Packaged Part: 20ETS Series

## Major Ratings and Characteristics

Parameters	Units	Test Conditions
$V_{FM}$ Maximum Forward Voltage	1.15 V	$T_J = 25^\circ\text{C}$ , $I_F = 20\text{ A}$
$V_{RRM}$ Reverse Breakdown Voltage	1600 V (**)	$T_J = 25^\circ\text{C}$ , $I_{RRM} = 100\text{ }\mu\text{A}$ (*)

(\*) Nitrogen flow on die edge.

(\*\*) Wafer and die Probe test clamped at 1200V to limit arcing. **1600V BV testable only in encapsulated packages**

## Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 $\mu\text{m}$ )
Chip Dimensions	207 x 157 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	330 $\mu\text{m}$ , $\pm 10\text{ }\mu\text{m}$
Maximum Width of Sawing Line	45 $\mu\text{m}$
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

# IR207DM16CCB

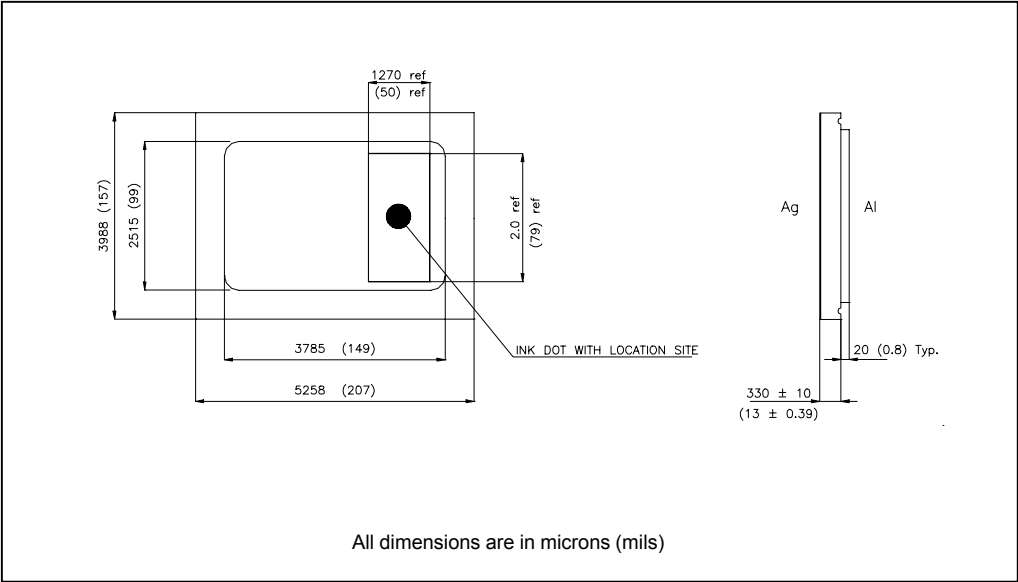
Bulletin I0140J 09/00

International  
**IR** Rectifier

## Ordering Information Table

Device Code						
IR	207	D	M	16	C	CB
1	2	3	4	5	6	7
1	- International Rectifier Device					
2	- Chip Dimension in Mils					
3	- Type of Device: D = Wire Bondable Standard Recovery Diode					
4	- Passivation Process: M = Glassivated MOAT					
5	- Voltage code: Code x 100 = $V_{RRM}$					
6	- Metallization: C = Aluminium (Anode) - Silver (Cathode)					
7	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier					

## Outline Table



**Wafer Layout**

